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This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1. (Presently Amended) A method for fabricating metal wirings, comprising the steps of:

forming a ground resin film by applying a resin onto an insulating substrate; patterning the ground resin film; and

forming a low-resistance metal film selectively on and over the patterned ground resin film by a wet film formation technique such that the low-resistance metal film encloses the patterned ground resin film, wherein the low-resistance metal film is a single layer film containing any one of Cu, Ni, Sn, Au, Ag, Cr, or Pd or the low-resistance metal film is a multilayer film containing at least one single layer film containing Cu, Ni, or Au.



- 2. (Original) A method according to Claim 1, wherein the ground resin film is made of a photosensitive resin that can be patterned by exposure and development.
 - 3. Cancelled.
- 4. (Original) A method according to Claim 1, wherein the ground resin film is made of polyimide.
- 5. (Original) A method according to Claim1, wherein plating is used as the wet film formation technique, and the ground resin contains a plating catalyst.
 - 6. (Original) A method according to Claim 1, further comprising:

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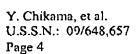
a step for, before the step of forming the low-resistance metal film, modifying a surface of the ground resin film.

- 7. (Original) A method according to Claim 6, further comprising:
 a set for, after the step of modifying the surface of the patterned ground resin film,
 forming on the surface-modified ground resin film a metal layer serving as a catalyst in the
 process of forming the low-resistance metal film by the wet film formation technique.
- 8. (Original) A method according to Claim 7, wherein the step of forming the metal layer acting as a catalyst in the process of forming the low-resistance metal film by the wet film formation technique comprises the steps of:

making metal ions adsorbed onto the surface-modified ground resin film; and reducing the metal ions.



- 9. (Original) A method according to Claim 6, wherein the ground resin film is made of a photosensitive resin which can be patterned by exposure and development.
 - 10. Cancelled.
- 11. (Original) A method according to Claim 6, wherein the ground resin film is made of polyimide.
- 12. (Original) The metal wiring fabricating method according to claim 11, wherein the step of modifying the surface of the patterned ground resin film is a process using KOH.
- 13. (Original) A method according to Claim 8, wherein the metal ions to be adsorbed onto the surface-modified ground resin are any one of Cu, Ag and Pd ions.



14. (Original) A method according to Claim 8, wherein

the step of reducing the metal ions is a process in which ultraviolet rays are irradiated to places where the low-resistance metal film is to be formed, by which the metal ions are selectively reduced.



15. (Previously added) The method according to claim 1, wherein the ground resin film has a thickness of between 0.05 μ m and 0.5 μ m.